



STGB19NC60HD - STGF19NC60HD STGP19NC60HD - STGW19NC60HD

19 A - 600 V - very fast IGBT

Features

- Low on-voltage drop ($V_{CE(sat)}$)
- Low C_{RES} / C_{IES} ratio (no cross-conduction susceptibility)
- Very soft ultra fast recovery anti-parallel diode

Applications

- High frequency motor controls
- SMPS and PFC in both hard switch and resonant topologies
- Motor drives

Description

This IGBT utilizes the advanced Power MESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

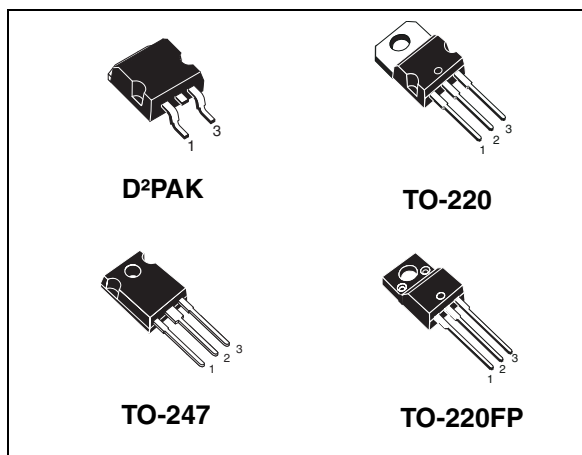


Figure 1. Internal schematic diagram

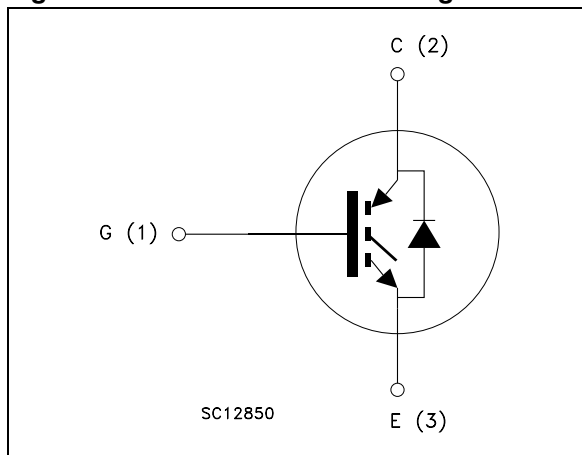


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGB19NC60HDT4	GB19NC60HD	D²PAK	Tape and reel
STGF19NC60HD	GF19NC60HD	TO-220FP	Tube
STGP19NC60HD	GP19NC60HD	TO-220	Tube
STGW19NC60HD	GW19NC60HD	TO-247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		TO-220 D ² PAK	TO-220FP	TO-247	
V _{CES}	Collector-emitter voltage (V _{GE} = 0)	600			V
I _C ⁽¹⁾	Collector current (continuous) at T _C = 25 °C	40	16	42	A
I _C ⁽¹⁾	Collector current (continuous) at T _C = 100 °C	19	10	21	A
I _{CL} ⁽²⁾	Turn-off latching current	40			A
I _{CP} ⁽³⁾	Pulsed collector current	40			A
I _F	Diode RMS forward current at T _C = 25 °C	20			A
I _{FSM}	Surge not repetitive forward current t _p =10 ms sinusoidal	50			A
V _{GE}	Gate-emitter voltage	±20			V
P _{TOT}	Total dissipation at T _C = 25 °C	130	32	140	W
T _j	Operating junction temperature	– 55 to 150			°C

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

2. V_{clamp}=80%V_{CES}, T_J= 150 °C, R_G=1 0 Ω, V_{GE} = 15 V

3. Pulse width limited by max. temperature allowed

Table 3. Thermal resistance

Symbol	Parameter	Value			Unit
		TO-220 D ² PAK	TO-220FP	TO-247	
R _{thj-case}	Thermal resistance junction-case max. IGBT	0.95	3.9	0.9	°C/W
	Thermal resistance junction-case max.diode	3.0	5.5	3.0	°C/W
R _{thj-amb}	Thermal resistance junction- ambient max	62.5		30	°C/W

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{BR(CES)}$	Collector-emitter breakdown voltage ($V_{GE}=0$)	$I_C=1\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE}=15\text{ V}$, $I_C=12\text{ A}$ $V_{GE}=15\text{ V}$, $I_C=12\text{ A}$, $T_C=125^{\circ}\text{C}$		1.8 1.6	2.5	V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE}=V_{GE}$, $I_C=250\text{ }\mu\text{A}$	3.75		5.75	V
I_{CES}	Collector cut-off current ($V_{GE}=0$)	$V_{CE}=600\text{ V}$ $V_{CE}=600\text{ V}$, $T_C=125^{\circ}\text{C}$			150 1	μA mA
I_{GES}	Gate-emitter leakage current ($V_{CE}=0$)	$V_{GE}=\pm 20\text{ V}$			± 100	nA
$g_{fs}^{(1)}$	Forward transconductance	$V_{CE}=15\text{ V}$, $I_C=12\text{ A}$		5		S

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE}=25\text{ V}$, $f=1\text{ MHz}$, $V_{GE}=0$		1180		pF
C_{oes}	Output capacitance			130		pF
C_{res}	Reverse transfer capacitance			36		pF
Q_g	Total gate charge	$V_{CE}=390\text{ V}$, $I_C=5\text{ A}$,		53		nC
Q_{ge}	Gate-emitter charge	$V_{GE}=15\text{ V}$,		10		nC
Q_{gc}	Gate-collector charge	Figure 20		23		nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390\text{ V}$, $I_C = 12\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, <i>Figure 21</i>		25 7 1600		ns ns A/ μ s
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390\text{ V}$, $I_C = 12\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_c = 125\text{ }^\circ\text{C}$ <i>Figure 21</i>		24 8 1400		ns ns A/ μ s
$t_{r(Voff)}$ $t_{d(Voff)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390\text{ V}$, $I_C = 12\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, <i>Figure 21</i>		27 97 73		ns ns ns
$t_{r(Voff)}$ $t_{d(Voff)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390\text{ V}$, $I_C = 12\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_c = 125\text{ }^\circ\text{C}$ <i>Figure 21</i>		58 144 128		ns ns ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on} $E_{off}^{(1)}$ E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390\text{ V}$, $I_C = 12\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, <i>Figure 21</i>		85 189 274		μ J μ J μ J
E_{on} $E_{off}^{(1)}$ E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390\text{ V}$, $I_C = 12\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_c = 125\text{ }^\circ\text{C}$ <i>Figure 21</i>		187 407 594		μ J μ J μ J

1. Turn-off losses include also the tail of the collector current

Table 8. Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on-voltage	$I_F = 12\text{ A}$ $I_F = 12\text{ A}, T_C = 125\text{ °C}$		2.6 2.1		V V
t_{rr}	Reverse recovery time	$I_F = 12\text{ A}, V_R = 40\text{ V},$ $di/dt = 100\text{ A}/\mu\text{s}$		31		ns
Q_{rr}	Reverse recovery charge			30		nC
I_{rrm}	Reverse recovery current	Figure 22		2		A
t_{rr}	Reverse recovery time	$I_F = 12\text{ A}, V_R = 40\text{ V},$ $T_C = 125\text{ °C}, di/dt = 100\text{ A}/\mu\text{s}$		59 102		ns nC
Q_{rr}	Reverse recovery charge					
I_{rrm}	Reverse recovery current	Figure 22		4		A

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

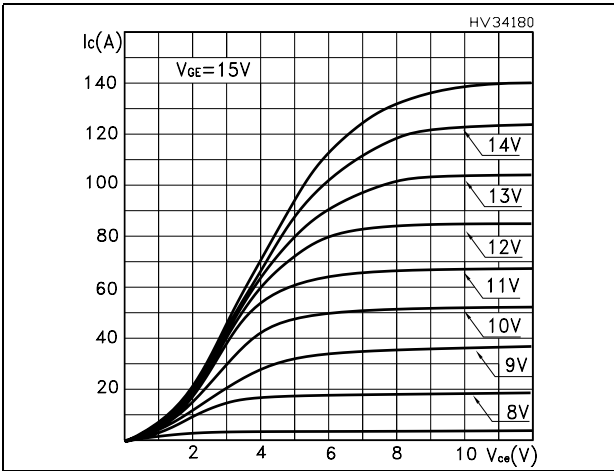


Figure 3. Transfer characteristics

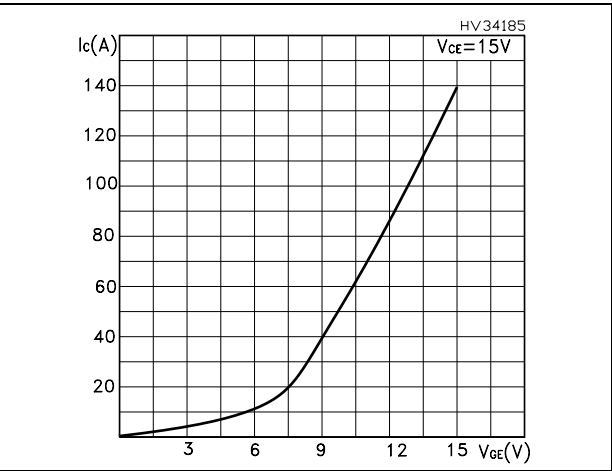


Figure 4. Transconductance

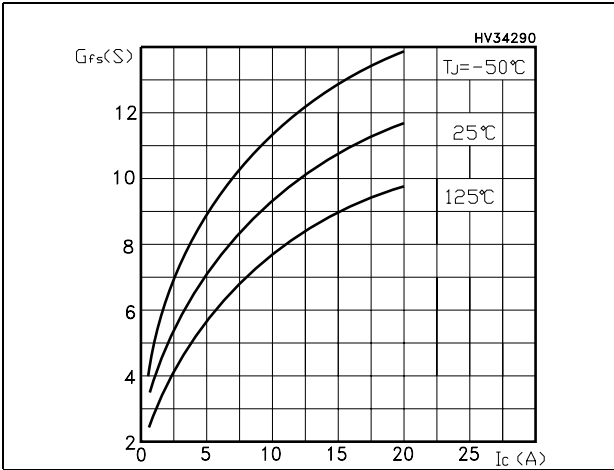


Figure 5. Collector-emitter on voltage vs temperature

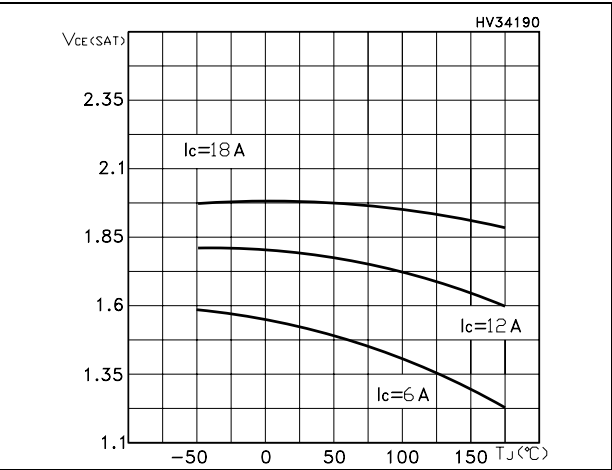


Figure 6. Gate charge vs gate-source voltage

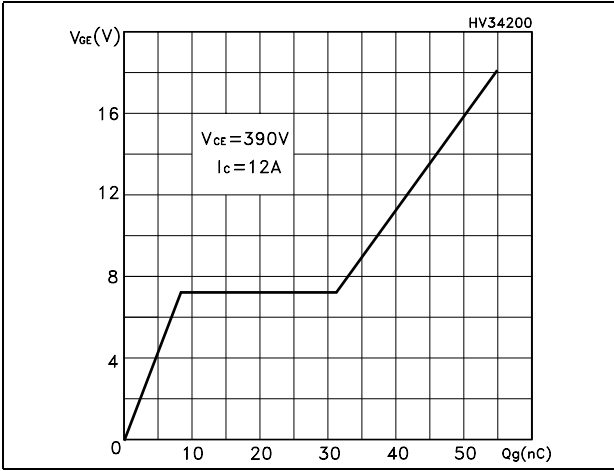


Figure 7. Capacitance variations

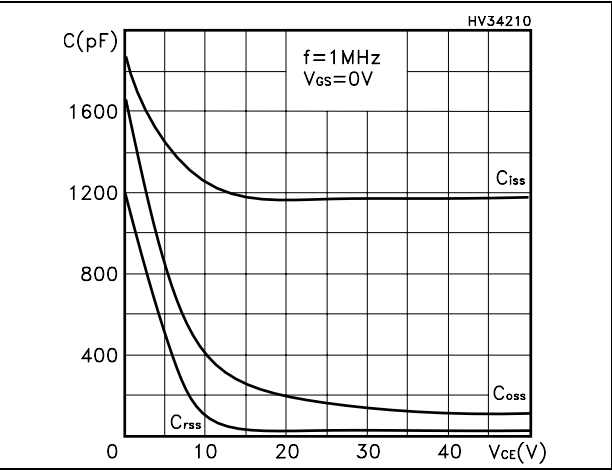


Figure 8. Normalized gate threshold voltage vs temperature

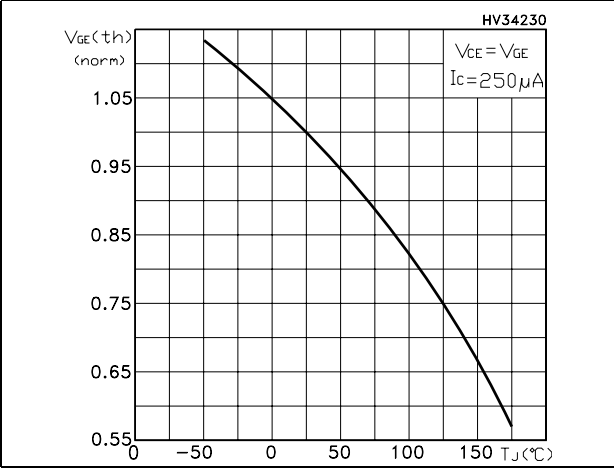


Figure 9. Collector-emitter on voltage vs collector current

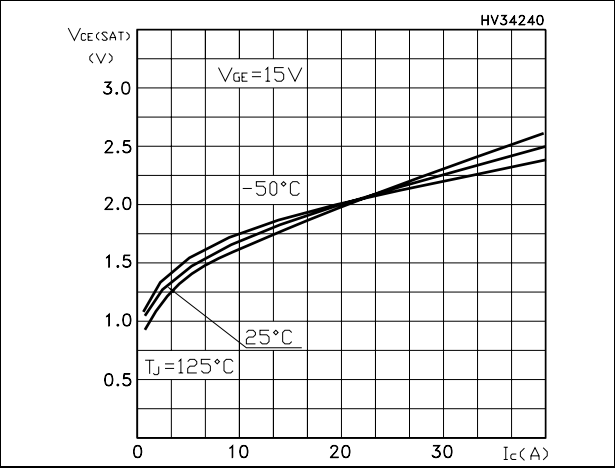


Figure 10. Normalized breakdown voltage vs temperature

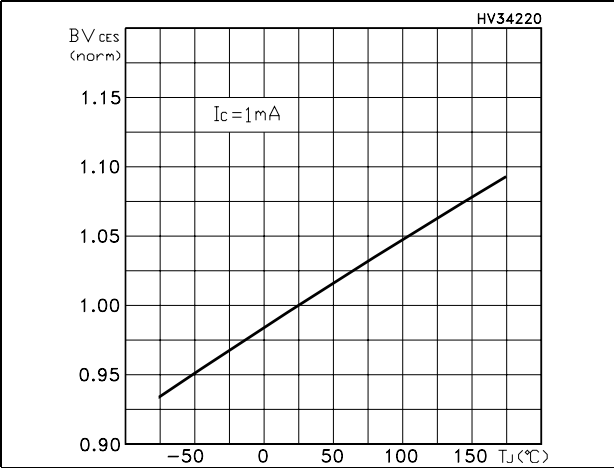


Figure 11. Switching losses vs temperature

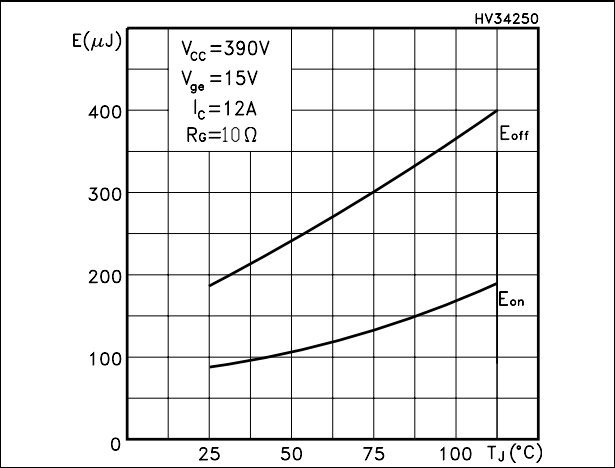


Figure 12. Switching losses vs gate resistance

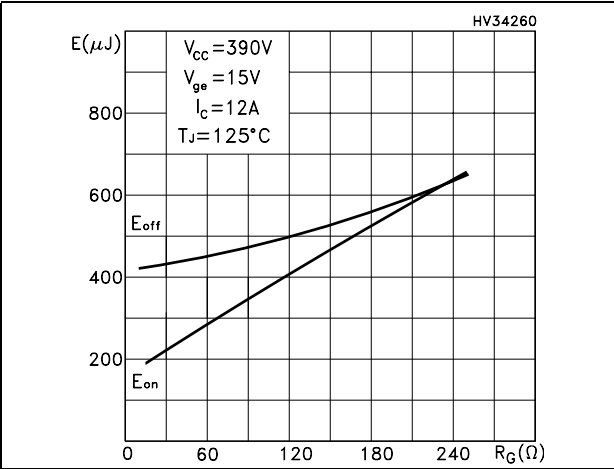


Figure 13. Switching losses vs collector current

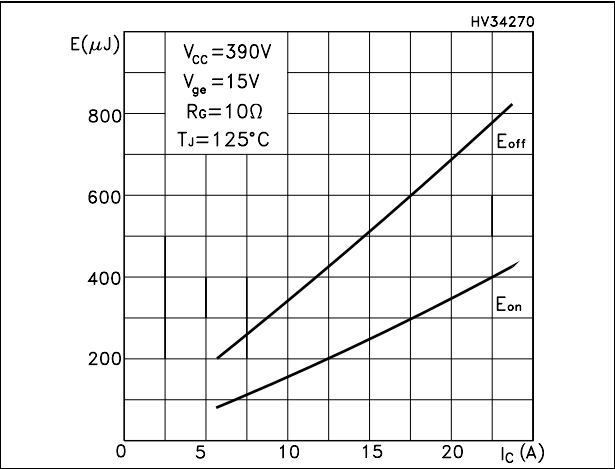


Figure 14. Turn-off SOA

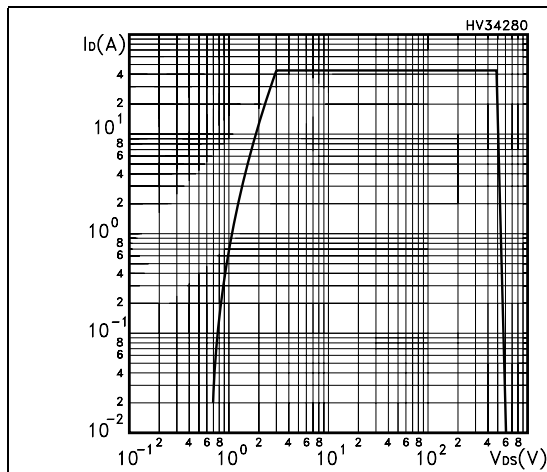


Figure 15. Forward voltage drop versus forward current

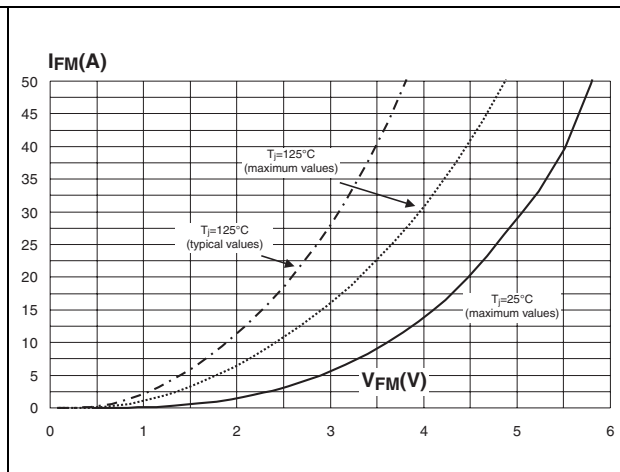
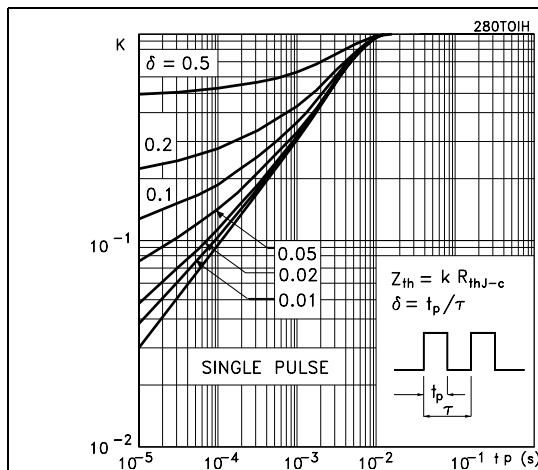
Figure 16. Thermal impedance for TO-220 D²PAK

Figure 17. Thermal impedance for TO-220FP

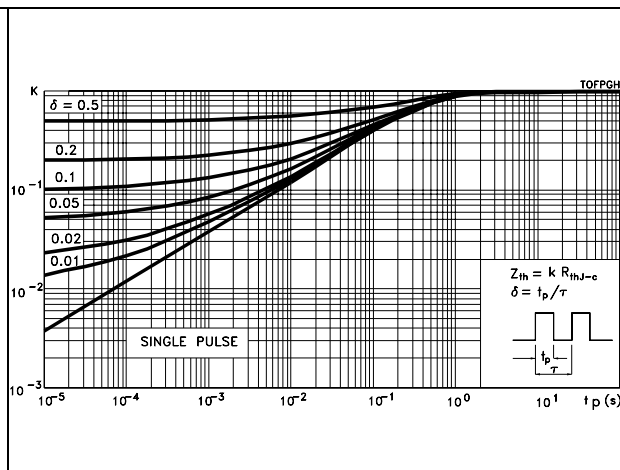
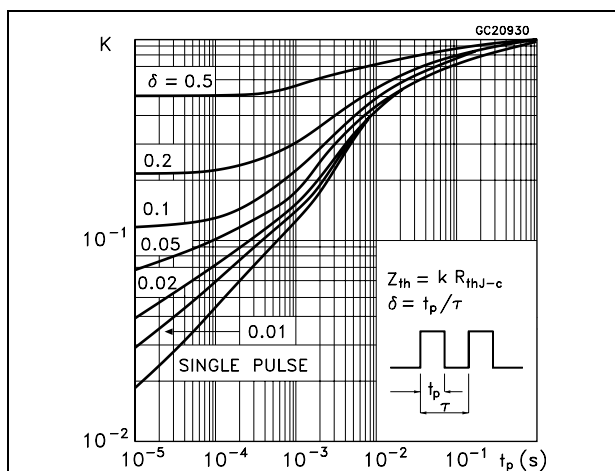


Figure 18. Thermal impedance for TO-247



3 Test circuits

Figure 19. Test circuit for inductive load switching

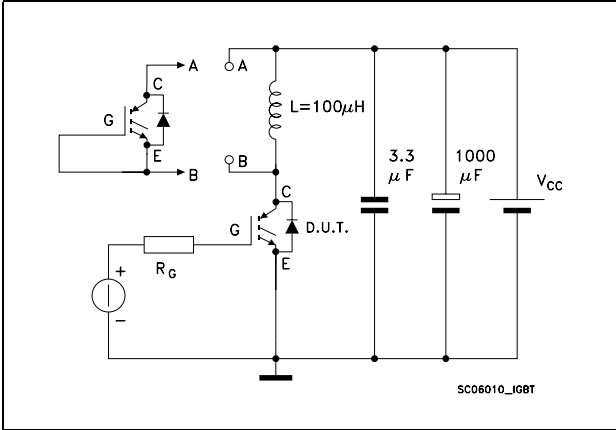


Figure 20. Gate charge test circuit

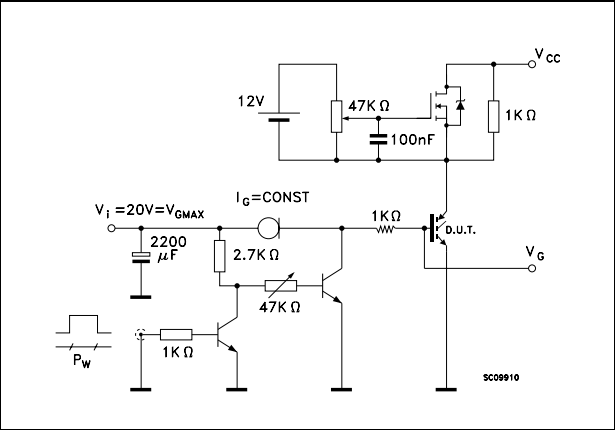


Figure 21. Switching waveform

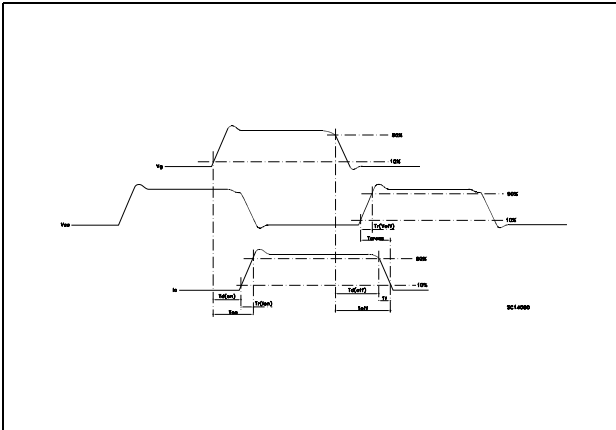
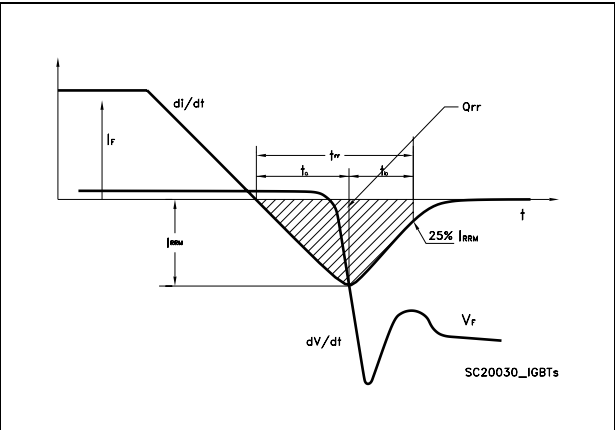


Figure 22. Diode recovery time waveform

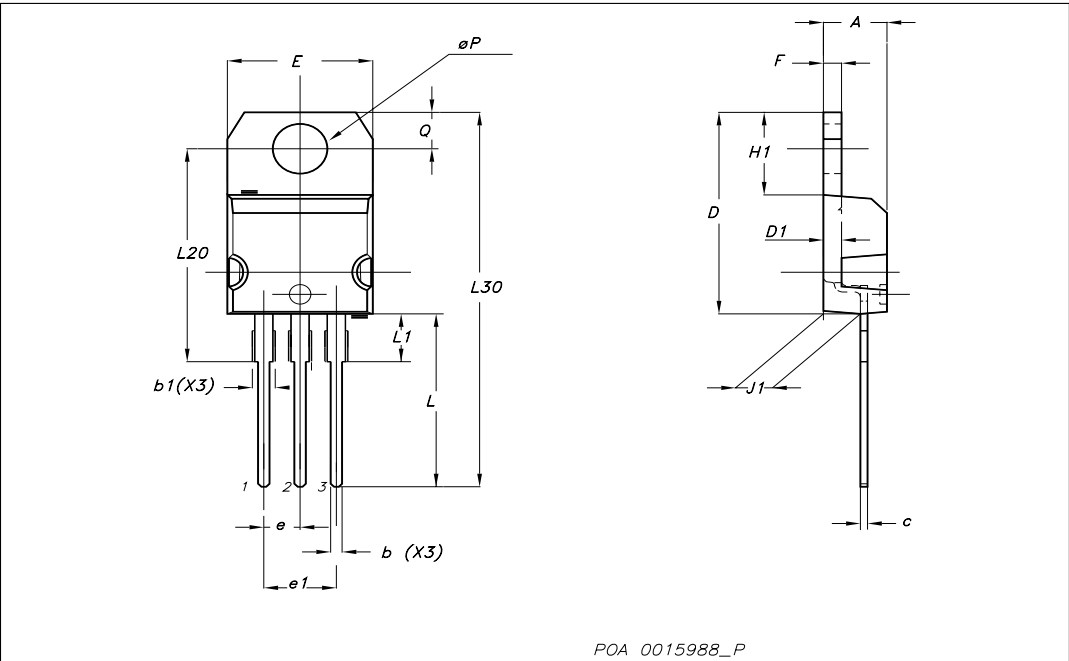


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

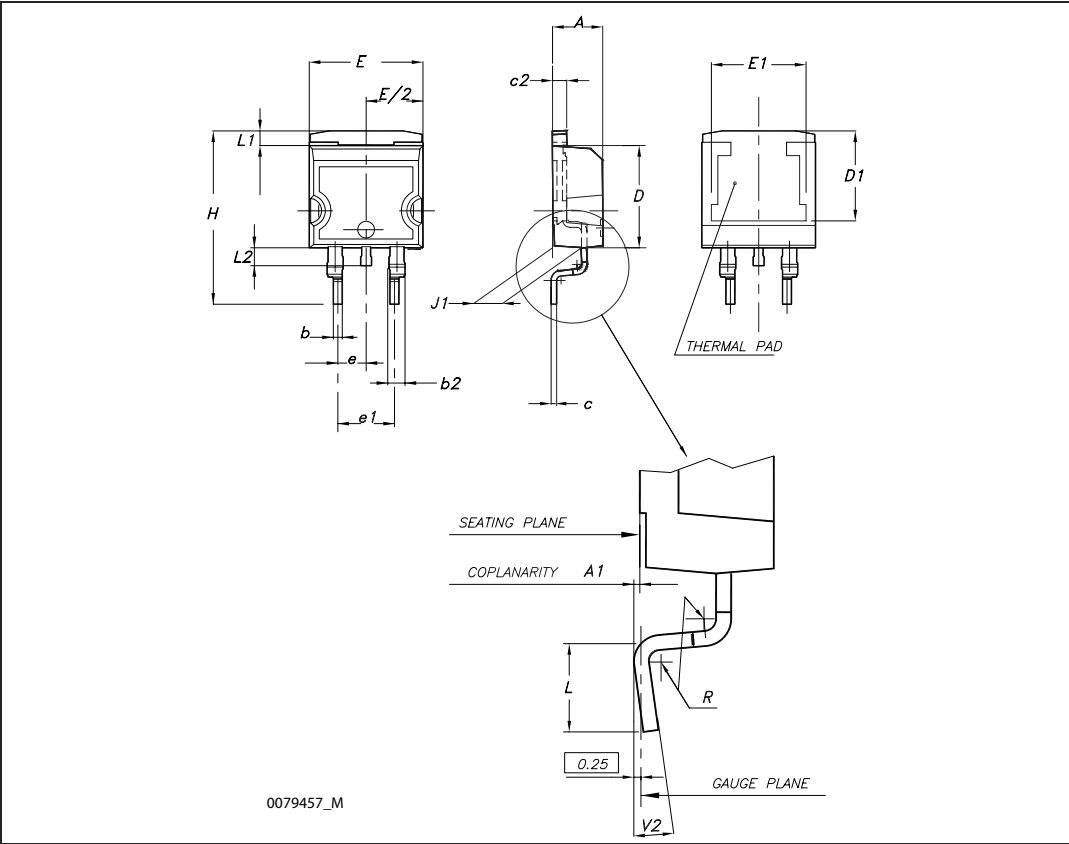
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



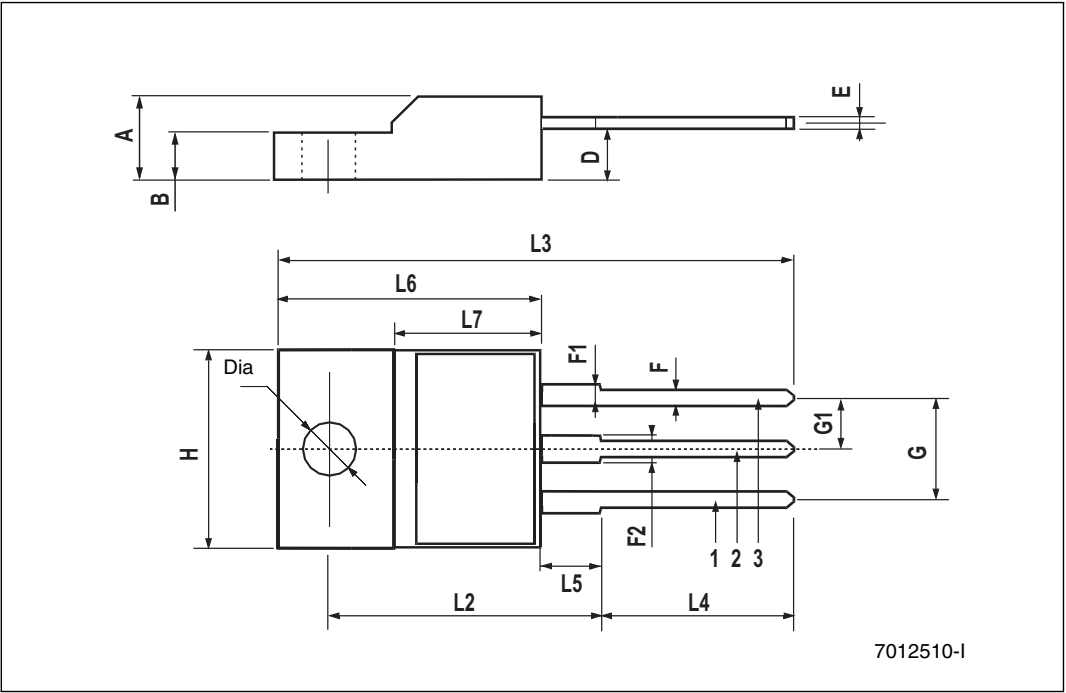
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



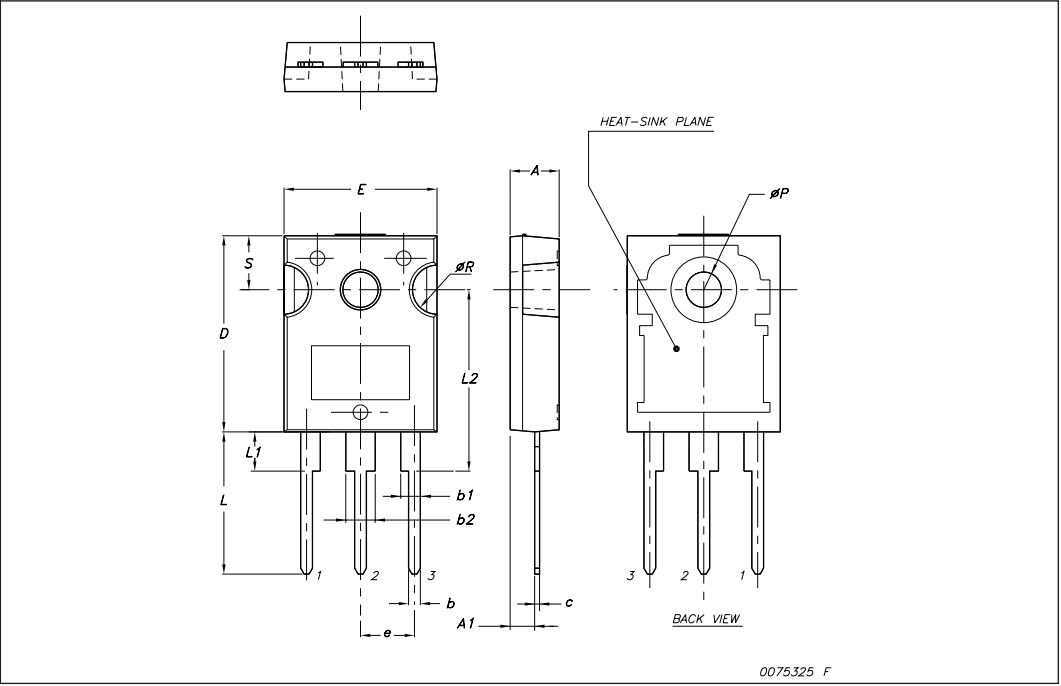
TO-220FP mechanical data

Dim.	mm.			inch		
	Min.	Typ	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.70	0.017		0.027
F	0.75		1.00	0.030		0.039
F1	1.15		1.50	0.045		0.067
F2	1.15		1.50	0.045		0.067
G	4.95		5.20	0.195		0.204
G1	2.40		2.70	0.094		0.106
H	10		10.40	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.80		10.60	0.385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.90		16.40	0.626		0.645
L7	9		9.30	0.354		0.366
Dia	3		3.2	0.118		0.126



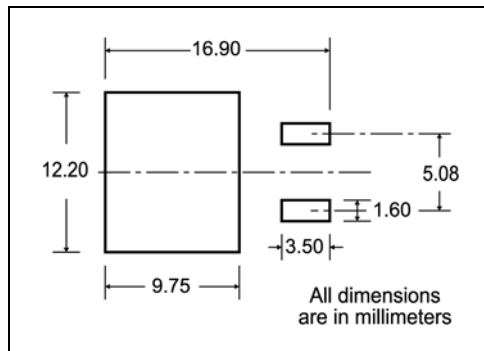
TO-247 mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	

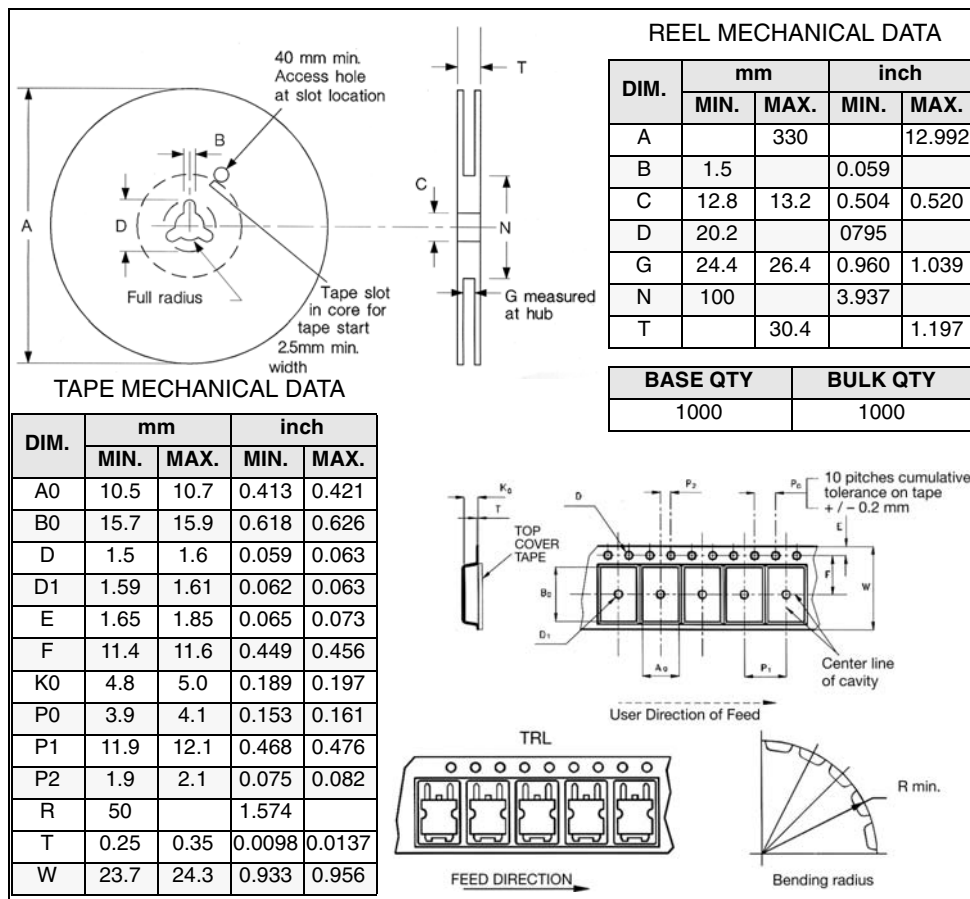


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 9. Document revision history

Date	Revision	Changes
02-Nov-2006	1	Initial release.
05-Jan-2007	2	Complete version
01-Jul-2008	3	– Modified: Table 2: Absolute maximum ratings – Inserted new packages, mechanical data: TO-220FP, TO-247

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